# Tom onaga{Luttinger param eters and spin excitations in the dim erized extended Hubbard model

Satoshi E jim a<sup>1</sup>, F lorian G ebhard<sup>1</sup>, and Satoshi N ishim oto<sup>2</sup>

<sup>1</sup>Fachbereich Physik, Philipps-Universitat Marburg, D-35032 Marburg, Germany <sup>2</sup>Max-Planck-Institut fur Physik komplexer System e, D-01187 Dresden, Germany (Dated: March 23, 2024)

We study the one-dimensional extended Hubbard model with alternating size of the hopping integrals using the density-matrix renormalization group method. We calculate the spin gap, the Tom onaga{Luttinger parameter, and the charge-density-wave order parameter for various dimerizations, interaction strengths, and band llings. At half band-lling the spin and charge excitations are gapped but these gaps disappear for in nitesimal hole doping. At quarter lling, the Um klapp scattering in the half-lled low er Peierls band generates a gap for the charge excitations but the gapless spin excitations can be described in terms of an elective antiferrom agnetic Heisenberg model. Beyond a critical strength for the nearest-neighbor interaction, the dimerized extended Hubbard model at quarter lling develops a charge-density-wave ground state. The dimerization and the nearest-neighbor C oulom b interaction strongly reduce the Tom onaga{Luttinger parameter from its value for the bare Hubbard model. We discuss the relevance of our notings for the Bechgaard salts.

PACS numbers: 71.10 Pm,71.10 Fd,78.30 Jw,72.15 N j

#### I. IN TRODUCTION

The Bechgaard salts are organic conductors which have attracted much interest over the last thirty years<sup>1,2</sup>. U pon variation of the pressure, the tem perature, and the anion X in (TMTSF)<sub>2</sub>X and (TMTTF)<sub>2</sub>X, these com pounds exhibit a rich phase diagram, e.g., a superconducting phase is found to lie in-between a param agnetic m etallic phase and a spin-density-wave phase. The system s can be regarded as quasione-dim ensional due to the strong anisotropy of the transport along the three crystalline axes. Recent experiments<sup>3</sup> support the view that the m etallic phase can be characterized as a Tom onaga { Luttinger liquid at tem peratures T > 100 K. Indeed, signatures of the Tom onaga {Luttinger liquid are the reduced density of states at the Ferm i energy as seen in angle-resolved photoem ission spectroscopy<sup>4,5</sup>, the negative tem perature dependence of the c-axis resistivity<sup>6</sup>, the scaling behavior of high-energy range of the optical conductivity<sup>7</sup>, the power-law tem perature dependence of the Hall coe cient<sup>8,9</sup>, and the empirical relationship  $(T_1T)^{-1} / \frac{2}{s}(T)$  between the measured spin relaxation rate and the magnetic susceptibility in nuclear magnetic resonance m easurem ents<sup>10,11</sup>. M oreover, distinctly different therm al conductivities for the charge and spin excitations have been reported which provide evidence for spin-charge separation<sup>12</sup>.

All correlation functions in the Tom onaga{Luttinger liquid display a power-law behavior with unusual, interaction-dependent coe cients. Many of them are sim – ple functions of the so-called Tom onaga{Luttinger param eter K . Most experiments give K 0.2 for the Bechgaard salts. The single-band Hubbard model in which spin-1/2 electrons move on a chain and interact only locally is one of the best studied Ham iltonians for correlated lattice electrons. However, the model gives K 0.5 for all interaction strengths which shows that the long-range parts of the C oulom b interaction m ust be taken into account for a proper description of the Bechgaard salts. In the extended Hubbard m odel the longrange parts of the C oulom b interaction are m in icked by a nearest-neighbor term  $^{13,14,15}$ .

O ther factors m ay also play an important role. For instance, the stacks of TM TTF and TM TSF m olecules form dimerized chains and the alternation of the electron transfer-matrix elements along the chain must be considered. Therefore, in this work we study the onedimensional extended Hubbard model with alternating hopping am plitudes, i.e., the one-dimensional dimerized extended Hubbard model as the minimal onedimensional, purely electronic model for the electronic excitations in the Bechgaard salts. The relevant bands in the TM TSF and TM TTF salts are led with three electrons so that the system is quarter- led in hole notation, and we use the hole picture in the following.

There are few system atic studies of the dimerized extended Hubbard model in the literature. Therefore, we investigate the model for various band llings, with an emphasis on the vicinity of the commensurate llings. In this way, our principle investigation of correlated electrons in quasi one-dimensional dimerized systems could be relevant also for otherm aterials, e.g., for the inorganic spin-Peierls system CuGeO<sub>3</sub><sup>16</sup>.

In our work we apply the density-m atrix renorm alization group (DMRG) m ethod which is one of the most reliable num ericalm ethods to study the low -energy properties of one-dim ensional correlated electron systems. W here applicable, we com pare our results to the predictions from eld theory and e ective single-band H ubbard m odels.

O ur paper is organized as follows. In Sec. II we dene the dimerized extended Hubbard model and introduce the physical quantities of interest, namely, the spin gap, the charge-density-wave (CDW) order parameter, and the Tom onaga{Luttinger parameter. In Sec. III, we separately present our DMRG results for the dimerized H ubbard m odel with and without the nearest-neighbor interaction, and discuss the experimental relevance of our investigations. We close with a short summary in Sect. IV.

#### II. MODELAND METHOD

#### A. Ham iltonian

In order to model the Bechgaard salts, we focus on the transport of a chain of stacked molecules and regard a single TMTTF or TMTSF molecule as a site. The chain has a geometrical (Peierls) modulation. Besides the intra-molecularCoulomb interaction, we should take into account a nearest-neighbor Coulomb repulsion because of the fairly short inter-molecular distance. Thus, our model Ham iltonian of choice is the one-dimensional dimerized extended Hubbard model for spin-1/2 electrons on L lattice sites

$$\hat{H} = \underbrace{\underbrace{k}}_{l} \underbrace{(\hat{C}_{l+1}^{V} \hat{C}_{l} + h \kappa;)}_{X} \underbrace{\underbrace{k}}_{l; \text{even}} \underbrace{(\hat{C}_{l+1}^{V} \hat{C}_{l} + h \kappa;)}_{l; \text{even}} \\ + \underbrace{\underbrace{U}_{n_{1^{*}} \hat{n}_{1\#}}_{l} + \underbrace{V}_{n_{1} n} (\hat{n}_{1} n) (\hat{n}_{1+1} n); \quad (1)$$

where  $C_1^V$  ( $\hat{c}_1$ ) is the creation (annihilation) operator of an electron with spin = ";# at site l,  $\hat{n}_1 = \hat{c}_1^V \hat{c}_1$  is the number operator, and  $\hat{n}_1 = \hat{n}_{1"} + \hat{n}_{1\#}$ . The total number of electrons is N = N<sub>"</sub> + N<sub>#</sub>, and n = N=L is the average number of electrons per lattice site. The electron transfer matrix elements  $t_1$  and  $t_2 < t_1$  model the dimerization of the chain, U is the strength of the Hubbard interaction, and V parametrizes the nearestneighbor C oulom b repulsion. We call a pair of sites which is connected by the hoping am plitude  $t_1$  a dimer'.

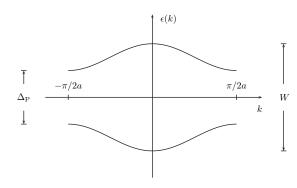


FIG. 1: Band structure for non-interacting electrons in a dimerized chain.

The dimerization splits the tight-binding cosine band into a bonding band ('lower Peierls band') and an antibonding band ('upper Peierls band'). The bare band structure is shown in Fig. 1. The dispersion relation of the two Peierls bands is given by

$$q = \frac{1}{t_1^2 + t_2^2 + 2t_1t_2 \cos k} \text{ for } kj = \frac{1}{2a}; (2)$$

where a is the lattice spacing which we set to unity in the following. The gap between the two Peierls bands is  $_{\rm P} = 2(t_1 \pm )$ . The total band width is  $W = 2(t_1 + t_2)$ . In the absence of a dimerization, for  $t_1 = t_2 = t$ , we recover the band structure of the tight-binding model in the reduced zone scheme.

## B. Physical quantities

In this work we employ the DMRG method which provides very accurate data for ground-state properties of one-dimensional correlated electron systems; for a review, see [17,18]. We use the DMRG to calculate the spin gap  $_{\rm s}$ , the CDW order parameter , and the Tom onaga{Luttinger parameter K . To this end, we consider a chain with L=2 dimers with L=2 even for a two-band system. We study chains with up to 320 sites and open-end boundary conditions. We keep up to m = 3600 density-matrix eigenstates in the DMRG procedure and extrapolate the calculated quantities to the limit m ! 1. In this way, the maximum error in the ground-state energy is below 10  $^{6}t_{1}$ . Lastly, we extrapolate our nite-size results to the them odynam ic limit, L ! 1.

The spin gap is de ned by

$$s = \lim_{L \ge 1} s(L);$$
  

$$s(L) = E_0(L; N + 1; N + 1) = E_0(L; N + ; N + ); (3)$$

where E  $_0$  (L;N  $_*$ ;N  $_{\#}) is the ground state energy of a system of length L with N <math display="inline">_*$  up-spin and N  $_{\#}$  down-spin electrons.

Later in this work, we shall focus on the CDW ground state of our model (1) at quarter band lling. For large enough nearest-neighbor repulsion V we expect a CDW with a wave vector  $Q_{CDW} = 4k_F$ . Here,  $k_F = n=2$  is the Ferm i wave number. At quarter band lling, n = 1=2, we have  $k_F = = 4$  which corresponds to a half-lled lower P eierls band.

The order parameter for the  $4k_{\rm F}$  -CDW phase is dened by

$$= \lim_{L \leq 1} (L);$$
 (4)

$$(L) = \frac{1}{r+2} \sum_{l=(L-r)=2}^{(L+X)=2+1} (1)^{l} h \hat{n}_{l} i :$$
 (5)

In (5) the sum m ation over the lattice sites l is restricted to a region r around the central site of the chain in order to reduce the edge e ects. W e set r = 2 for a system atic extrapolation to the therm odynamic limit. Of course, the extrapolated results should be independent of the choice of the range r. On nite lattices and for openend boundary conditions, the Friedel oscillations from the edges result in a nite value for (L), and a wellcontrolled nite-size extrapolation is mandatory.

For the calculation of the Tom onaga {Luttingerparam eter K we use a new method which we proposed recently<sup>19</sup>. The Tom onaga {Luttingerparam eter K determines the long-range decay of the density-density correlation function in the metallic Tom onaga {Luttinger liquid ground state. It is de ned by the ground-state expectation value

$$C^{NN}(r) = \frac{1}{L} \sum_{l=1}^{K^{L}} \hat{m}_{l+r} \hat{n}_{l} i \hat{m}_{l+r} i \hat{m}_{l} i$$
 (6)

U sing conform all eld theory it can be show  $n^{20,21}$  that the asymptotic behavior for 1 r L is given by

$$C^{NN}(r) = \frac{K}{(r)^2} + \frac{A\cos(2k_F r)}{r^{1+K}} \ln^{3=2}(r) + ;$$

where A is a constant. In previous approaches<sup>22,23,24,25</sup>, K was extracted from the Fourier transformation of  $C^{NN}$  (r) but in a real-space DMRG approach the accuracy of the correlation function becomes increasingly worse as the distance r increases. In Ref. [19] we calculated the density-density correlation function directly in Fourier space. We address

N (q) = 
$$\frac{2}{L} h\hat{n}$$
 (q) $\hat{n}$  (q) $\hat{i}$ ; (8)

where fi (q) is given by

$$n (q) = \sum_{\substack{l \neq 0 \text{ dd}}}^{X} e^{i(q=2)(l+1=2-r_{c})} (c_{l}^{y} c_{l} + c_{l+1}^{y} c_{l+1}) : (9)$$

Here,  $r_c = (L + 1)=2$  denotes the central position of the chain. The derivative of N (q) at q = 0 directly gives the Tom onaga{Luttinger parameter. In practice, we obtain it from

$$K = \lim_{L \ge 1} K (L);$$
  

$$K (L) = \frac{L}{4}N \frac{4}{L}:$$
 (10)

For a precise calculation of K is important to target not only the ground state  $j_0i$  but also the state  $j_qi = \hat{n}(q)j_0i$  in the DMRG procedure; see Ref. [19] for further details.

The Tom onaga{Luttinger parameter is well de ned only for the metallic Tom onaga{Luttinger liquid. Later we shall investigate K for insulators which are in nites-im ally doped away from their commensurate doping  $n_c$ . In these cases we give

K (n ! 
$$n_c$$
) =  $\lim_{L! \ 1}$  K n =  $n_c \ \frac{2}{L}$  : (11)

T his approach is very successful for the single-band H ubbard m odel, as dem onstrated in Ref. [19].

## C. E ective models

For not too sm all dimerizations,  $t_2=t_1 < 0.9$ , we can map the dimerized extended Hubbard model to an e ective single-band extended Hubbard model<sup>13</sup>. The upper Peierls band can be integrated out and we are left with a Hubbard chain with L=2 dimersites  $l_d$  with e ective parameters,

$$\hat{H}_{e} = t_{e} \begin{pmatrix} X & X \\ (\hat{C}_{l_{d}+1}^{V} \hat{C}_{l_{d}} + h c;) + U_{e} & \hat{n}_{l_{d}} \\ & & I_{d} \\ + V_{e} & (\hat{n}_{l_{d}} 1) (\hat{n}_{l_{d}+1} 1); \end{pmatrix}$$
(12)

$$t_e = \frac{t_2}{2}; \qquad (13)$$

$$U_{e} = 2t_{1} \frac{P (U - V) + 16t_{1}^{2}}{2} (U + V); \quad (14)$$

(7) 
$$V_e = \frac{V}{4}$$
: (15)

The band lling is  $n_e = 2n$  so that  $k_{F,e} = n$  and  $v_{F,e} = t_2 \sin(n)$ . Note that  $U_e = t_e$  can be large even when  $U = t_1$  is small, e.g.,  $U_e = t_e = 8.8$  for  $U = t_1$ , V = 0, and  $t_2 = t_1 = 0.1$ .

For V < V<sub>c</sub> the quarter- led dimerized extended Hubbard model describes a Mott{Hubbard insulator with gap-less spin excitations. In this parameter region, the spin degrees of freedom of the e ective single-band Hubbard model (12) can be described by an e ective Heisenberg model,

$$\hat{H}_{heis;e} = J_{e} \sum_{l_{d}}^{X} \hat{S}_{l_{d}} \hat{S}_{l_{d}+1};$$
 (16)

where  $\hat{S}_{l_d}$  is the spin operator for a dimer located at position  $l_d$ . Up to second-order in  $t_2=U_e$ , we have

$$J_{e} (V) = \frac{4t_{2}^{2}}{8t_{1} + 2U + V} \frac{1}{2} (U - V)^{2} + 16t_{1}^{2} : (17)$$

#### III. RESULTS

#### A. D im erized H ubbard m odel

First, we consider the dimerized Hubbard model, i.e., we set V = 0 in (1).

#### 1. Tom onaga { Luttinger param eter

In order to demonstrate the accuracy of our method, we address the Tom onaga{Luttinger parameter at small interactions, U < W, as a function of the dimerization in the metallic regime, n = 0.4. To lowest order in the

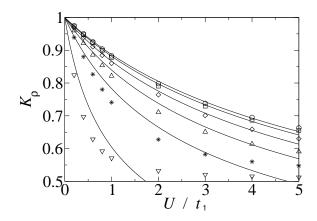


FIG.2: Tom onaga{Luttinger parameter K from the DMRG approach (symbols) in comparison with the predictions from the g-ology method (solid lines), as a function of U=t<sub>1</sub> for  $t_2=t_1 = 1;0.9;0.5;0.3,0.1$  (from top to bottom) at n = 0.4 for the dimerized H ubbard model.

couplings,  $g_1 = g_2 = g_4 = U=2$ , the eld-theoretical gology' approach predicts<sup>26,27</sup>

$$K = \frac{1}{2} \frac{2 v_{\rm F}}{v_{\rm F} + U}$$
(18)

where the Ferm i velocity  $v_{\rm F}\,$  is given by

$$v_{\rm F} = \frac{t_1 t_2 \sin k_{\rm F}}{t_1^2 + t_2^2 + 2t_1 t_2 \cos(k_{\rm F})} :$$
(19)

T his result can be system atically in proved with the functional R enorm alization G roup m ethod  $^{28}$  .

In Fig.2, we compare the Tom onaga {Luttingerparam – eter as calculated from the DMRG approach, eq. (10), to the g-ology prediction (18). We plot K as a function of  $U=t_1$  for various dimerization strengths  $t_2=t_1$  at band lling n = 0.4. The system is metallic for all interaction strengths. For all dimerizations, K decreases m onotonically with increasing C oulom b interaction and

nally approaches K (U ! 1) = 1=2, as expected from the nondimerized Hubbard model. For small dimerization,  $t_2=t_1 > 0.5$ , the DMRG results agree very well with those from the g-ology approach for all U < W. For small U= $t_1$ , K decreases weakly and monotonically with  $t_2=t_1$ . This can be understood from the corresponding decrease of the bandwidth, W = 2( $t_1 + t_2$ ), with a corresponding reduction of the Fermi velocity.

W hen the dimerization is large,  $t_2=t_1 < 0.5$ , and the H ubbard interaction is large, U > W = 2, the results from g-ology substantially deviate from the numerically exact D M RG results. The Tom onaga{Luttinger parameter K decreases rapidly with decreasing  $t_2=t_1$ , and the g-ology predictions quickly violate the constraint K 1=2. Apparently, higher-order corrections in U=W beyond the one-loop calculations needed to be considered.

A sournext application, we investigate the Tom onaga{ Luttinger parameter as a function of the band lling and the interaction strength. In Fig. 3, we show K from the

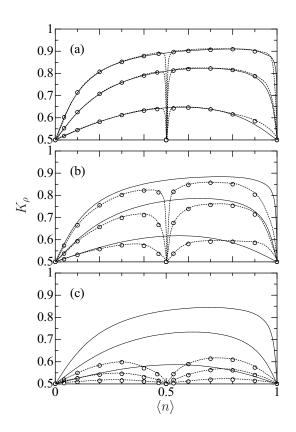


FIG. 3: Tom onaga{Luttinger parameter K as a function of the band-lling n for various dimerizations: (a)  $t_2=t_1 = 0.9$ , (b)  $t_2=t_1 = 0.5$ , and (c)  $t_2=t_1 = 0.1$ . In each gure,  $U=t_1 = 1;2;6$  from top to bottom. Open circles denote the DMRG results in the dimerized H ubbard m odel, and dotted lines are guides for eyes. Solid lines give the exact result for the single-band H ubbard m odel with hopping integral  $t = (t_1 + t_2)=2$ .

DMRG method as a function of n for various interaction strengths  $U=t_1$  and dimerizations: (a)  $t_2=t_1 = 0.9$ , (b)  $t_2=t_1 = 0.5$ , and (c)  $t_2=t_1 = 0.1$ . For comparison we also plot the exact results for K from the Bethe Ansatz for the one-dimensional single-band H ubbard m odel with the same band width,  $t = (t_1 + t_2)=2$ .

W hen the dimerization is small,  $t_2=t_1=0.9$ , we again nd a good general agreem ent between the results for the dimerized Hubbard model and the single-band Hubbard model with the same total bandwidth. An exception is the narrow range around quarter band lling, n = 1=2. At quarter lling, the lower Peierls band is half lled and the Um klapp scattering becomes a (marginally) relevant perturbation which turns the metallic phase into a Mott{ Hubbard insulator where K is not well de ned, and we give the value for in nitesim al doping, see eq. (11). As expected from eld theory<sup>27,29</sup>, and con med numerically, we have

K 
$$n = \frac{1}{2} = \frac{1}{2}$$
 (20)

for the density-driven M ott transition for all interaction strengths. This follows from the mapping of the quarter-

led dimerized Hubbard model to the e ective singleband Hubbard model at halfband-lling. Therefore, K strongly changes as a function of density in the vicinity of quarter lling even for small dimerizations. The e ect becomes more prominent with increasing dimerization strengths, see Fig. 3b.

W hen the dimerization is large,  $t_2 = t_1 = 0.1$ , the singleband Hubbard model does not provide a good starting point for the analysis anymore. Instead, for large  $t_1 = t_2$  we rather consider the e ective single-band Hubbard model (12) for V = 0. Because of the strong e ective on-site interaction  ${\tt U}_{\rm e}\,$  =t\_e  $\,$  , the U m k lapp scattering strength becom es very large. For instance, the e ective couplings at  $t_2 = t_1 = 0$ :1 are estimated from eq. (14) as  $U_e = t_e = 8.8; 15:3; 27:9$  for V = 0 and  $U = t_1 = 1; 2; 6$ , respectively. Therefore, the values for K are rather small for all  $U = t_1 > 1$ . Moreover, the e ective singleband Hubbard model always gives the correct result K (n = 1=2) = 1=2 because the quarter-led dim erized Hubbard m odelm apsonto the half- lled single-band Hubbard model which describes a Mott {Hubbard insulator for all interaction strengths.

As seen in Fig. 4, the quantitative agreement for K from the dimerized Hubbard model and the elective single-band Hubbard model is quite good for all  $U = t_1$  at  $t_2 = t_1 = 0.1$ . Note that the elective Hubbard model displays its particle-hole symmetry around n = 1=2 which the dimerized Hubbard model obeys only for  $t_2 = t_1 ! 0$  or  $U = t_1 ! 1$ .

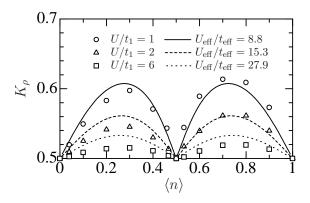


FIG.4: Tom onaga{Luttinger parameter K from the DMRG approach for large dimerization,  $t_2=t_1=0:1$ , in comparison with the analytical result for the e ective single-band Hubbard m odel. Recall that the band lling n of the dimerized Hubbard m odel corresponds to a lling 2n for the e ective single-band Hubbard m odel.

## 2. Spin excitations

As our second quantity of interest we study the spin degrees of freedom at and around some commensurate band llings. At half lling, n = 1, the dimerized Hubbard model is a band-M ott insulator for all  $U=t_1 > 0$ , and we expect a nite gap for spin excitations for all  $U=t_2$ .

For small interaction strengths, the spin gap is of the order of the Peierls gap,  $_{\rm s}$  (U=t<sub>1</sub> ! 0) =  $_{\rm P}$  = 2(t<sub>1</sub>  ${\rm t}_{\rm p}$ ). For large interactions, the spin degrees of freedom of the dimerized H ubbard m odel can be described by the one-dimensional Peierls{H ubbard m odel so that the spin gap to low est order in t<sub>1</sub>=U becomes

$$_{\rm s}$$
 (t<sub>1</sub>=U ! 0) /  $\frac{4t_1^2}{U}$   $\frac{t_1^2}{t_1^2 + t_2^2}$  ; (21)

in accordance with the results for the corresponding Peierls{Heisenberg model<sup>30</sup>. Eq. (21) is applicable for  $U=t_1 > 4$ . In the inset of Fig. 5 we show two examples for the nite-size scaling of the spin gap (3),  $(t_2=t_1 = 0.5; U=t_1 = 10)$  and  $(t_2=t_1 = 0.9; U=t_1 = 5)$ . The dependence of the gap on the system size is quite small because in the ground state individual spin singlets are formed on the dimens so that the gapped spin excitations are rather localized in space.

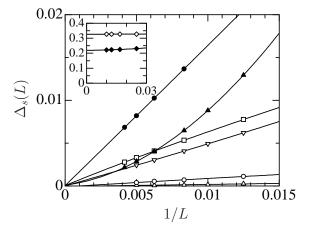


FIG. 5: Extrapolation of the spin gap  $_{\rm s}$  (L) of the dimerized H ubbard m odel. Solid symbols represent the results for weak dimerization ( $t_2=t_1=0.9$ ,  $U=t_1=5$ ) at in nitesimal doping of the band-M ott insulator (n = 1, triangles) and at small doping (n = 0.95, circles). Open symbols give the results for interm ediate dimerization ( $t_2=t_1=0.5$ ,  $U=t_1=10$ ) at in nitesimal doping of the band-M ott insulator (n = 1, triangles), at the electron densities n = 0.95 (circles), n = 0.8 (squares), and at in nitesimal doping of the M ott{H ubbard insulator at quarter lling (n = 0.5, lower triangles).

Inset: Extrapolation of the spin gap of the band-M ott insulator at half band-lling for  $(t_2=t_1 = 0.9, U=t_1 = 5)$  (solid diam onds) and for  $(t_2=t_1 = 0.5, U=t_1 = 10)$  (open diam onds).

It is more interesting to study the doping dependence of the spin gap. In Fig. 5 we plot  $_{\rm s}$  (L) as a function of system size for ( $t_2=t_1=0.5; U=t_1=10$ ) and for ( $t_2=t_1=0.9; U=t_1=5$ ) for several band llings. As seen from the gure, the spin gap vanishes for all electron densities. In particular, at half band-lling it disappears as soon as the system is doped with an in nitesim alam ount of holes. This can be understood in terms of the spin excitations of a half-lled system with two holes. Let us assume that the two holes are con ned to a dimer. Then, a spin excitations would remain the same local excitation as in the perfectly half-lled system which costs the nite energy (21). However, the holes are actually delocalized over the system because the breaking of two spin dimers cost twice  $_{\rm s}$  but the gain in kinetic energy is approximately

$$E_{it} / 2(t_1 t_2)$$
: (22)

 $E_{\pm}$  is always larger than 2 s. The mobile holes leave behind at least two broken spin dimens whose spin excitation energy vanishes in the therm odynam ic limit.

Apparently, the dimerized Hubbard behaves di erently from the two-leg Hubbard ladder at half band-lling where a spin-singlet pair is formed on each rung. The spin gap in the ladder system remains nite for nite hole doping. There the spin-singlet pairs them selves are mobile so that in the ground state an additional pair of holes is actually con ned to a rung because the gain in kinetic energy due to the hole motion is smaller than the combined loss in the pairing energy and the kinetic energy of the spin dimers.

Finally, we investigate the spin gap for the quarterlled dimerized Hubbard model at in nitesimal doping. In Fig. 5 we plot the size-dependence of the spin gap for the in nitesimally doped Mott{Hubbard insulator at quarter lling for  $(\underline{t}=t_1 = 0.5; U=t_1 = 10)$ . The extrapolated values are zero for all dimerization and interaction strengths. Therefore, the spin-gap liquid, suggested in the one-dimensional dimerized t-J model<sup>31</sup> is not realized in the dimerized Hubbard model.

#### B. D im erized extended H ubbard m odel

Now we turn to the case V  $\notin$  0 in (1). We focus on the region around quarter lling where the nearest-neighbor interaction can lead to a CDW phase. This is known for the extended H ubbard m odel whose ground-state phase diagram was studied in detail recently<sup>14,19</sup>.

### 1. Charge order

P revious studies<sup>32,33,34</sup> suggested that the presence of a dimerization suppresses the CDW phase. Therefore, we investigate the dependence of the critical coupling V<sub>c</sub> for the onset of the CDW . To this end we calculate the CDW order parameter from (5) as a function of the dimerization strength.ForV = 0 we have = 0 whereas, for large V, the CDW order parameter approaches its classical value, (V ! 1) = 0.5.

In Fig. 6 we show the order parameter (V) as a function of  $V=t_1$  for dimerizations  $t_2=t_1 = 1;0:9;0:5;0:1$  for

xed  $U=t_1 = 10$  at quarter band lling. In the absence of a Peierls modulation,  $t_2=t_1 = 1$ , i.e., in the extended single-band Hubbard model, (V) is nite above  $V_c=t_1 = 2.65$ , in agreement with previous work<sup>14,19,35</sup>.

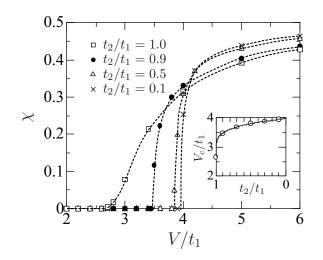


FIG.6: CDW order parameter extrapolated to the thermodynamic limit L ! 1 for  $t_2=t_1 = 1, 0.9, 0.5$ , and 0:1 with xing U= $t_1 = 10$  at quarter lling. Lines are guides to the eyes. Inset: Estimated critical interaction strength  $V_c=t_1$  for the CDW transition as a function of  $t_2=t_1$ .

Apparently, the dimerization enhances the charge uctuation on each dimer, and, consequently the tendency towards charge order is reduced.

In the presence of a dimerization the critical value for the onset of the CDW increases with increasing dimerization. Moreover,  $(V;t_2=t_1 < 1)$  rises up sharply above  $V_c(t_2=t_1)$  even when  $t_2=t_1$  is close to unity. We speculate that the transition remains continuous for all nite  $t_2=t_1$  but the slope is in nite for all  $t_2=t_1 > 0$ . In the inset of F ig. 6 we show the critical value  $V_c=t_1$  as a function of the dimerization strength  $t_2=t_1$ . We not that  $V_c=t_1$  changes rapidly for small  $t_2=t_1$  and quickly saturates at its classical value for  $t_2=t_1 = 0$ . The value  $V_c(t_2=t_1 = 0) = 4t_1$  is readily explained by considering an isolated dimer. In the isolated-dimer limit the energies of the Mott{Hubbard insulator and the CDW insulator are

$$E_{0}^{\text{MH}} = L = t + V_{e} = t + V = 4; \quad (23)$$

$$E_0^{CDW} = L = 0;$$
 (24)

so that the criterion for the (discontinuous) transition is  $E_0^{M H}$  (V<sub>c</sub>) =  $E_0^{C D W}$  (V<sub>c</sub>) which immediately gives V<sub>c</sub>=t<sub>1</sub> = 4.

#### 2. Tom onaga { Luttinger param eter

In the absence of a dim erization, the Tom onaga{Luttinger parameter decreases as a function of V=t for xed U=t> 4 and reaches K = 0.25 at the critical coupling. W hen the CDW insulator is in nitesimally doped the system m etalizes and K <sup>CDW</sup> =  $1=8^{19,29,36}$ .

For a nite dimerization, the quarter-lled system is a Mott{Hubbard insulator for small  $V=t_1$  and nite  $U=t_2$ . At in nitesimal doping we nd  $K^{MH}$  ( $V < V_c$ ) = 1=2 below the transition, independent of V. This is readily understood from the fact that the e ective model is the extended single-band H ubbard model at halfband-lling for which the eld-theoretical arguments for a density-driven M ott transition still apply. A qualitatively and quantitatively di erent behavior emerges from the transition to the CDW insulator at  $V_c$ . The Tomonaga Luttinger parameter drops from K = 1=2 in the innitesimally doped M ott{H ubbard insulator to K <

1=8, as we shall discuss in more detail now.

The dimerization has two prominent e ects on K . First, it increases the strength of the Um klapp scattering which makes K smaller. Second, the dimerization suppresses the CDW instability which tends to make K larger. These e ects are most apparent around quarter

lling where the two tendencies compete with each other close to the CDW instability. Both e ects increase upon decreasing  $t_2=t_1$ . The rst e ect continues to develop progressively and leads to  $U_e = t_e$  ! 1 as  $t_2=t_1$  ! 0. A s shown in Sect. IIIB 1, the second e ect develops fast as a function of the dimerization and quickly saturates. Therefore, we expect that the rst e ect, a reduction of K upon dimerization, is more prominent but for quarter

lling and in the vicinity of the transition to the CDW phase.

The reduction of K with dimerization can actually be inferred from the g-ology approach where the Tom onaga-Luttinger parameter near quarter lling is given by

$$K \qquad \frac{r}{2 v_{\rm F} V} \qquad (25)$$

with  $v_F = t_1 t_2 = \frac{p}{t_1^2 + t_2^2}$ . The formula shows that K decreases monotonously as a function of V and of  $t_2 = t_1$ . Naturally, g-ology cannot cover large dimerizations or the transition region where the increase of K (V) upon dimerization becomes apparent.

In Fig. 7 we present the DMRG results for K as a function of V=t1 at a hole doping and an electron doping of 5%, hni = 0.50:025, for  $U = \frac{1}{4} = 6$  and various dim erizations. The num erically exact DMRG results con m the general expectations as expressed in the gology form ula (25). The Tom onaga { Luttinger param eter decreases m onotonously with  $V=t_1$  for all dim erizations and, in general, it decreases as a function of  $t_2 = t_1$ for xed V=t. The fact that K is alm ost independent of  $t_2=t_1$  for xed  $1 < V=t_2 < 2$  can be attributed to the above-m entioned com petition between the Um klapp scattering and the charge ordering. For certain param eter regions, a change in the dim erization strength has almost no net e ect on K because a change in the strength of the Um klapp scattering is compensated by a change in the mobility of the charge carriers. For the same param eter set  $(V = t_1; t_2 = t_1)$ , K is generally som ew hat smaller for the hole-doped case than for the electron-doped case but there is no di erence in the qualitative behavior. This had to be expected because the system is particle-hole symmetric around quarter lling to low est order in  $t_2 = t_1$ . From now on we shall focus on the case of hole doping.

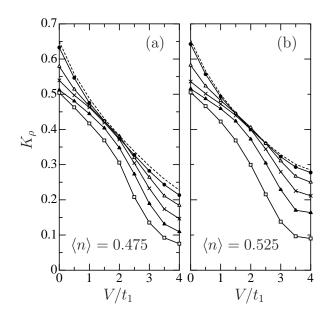


FIG. 7: Tom onaga{Luttinger parameter K in the dimerized extended Hubbard model as a function of the nearest-neighbor C oulom b interaction  $V=t_1$  for  $U=t_1 = 6$  and various dimerizations:  $t_2=t_1 = 1$  (dashed line),  $t_2=t_1 = 0.9$  (lled circles),  $t_2=t_1 = 0.7$  (open triangles),  $t_2=t_1 = 0.5$  (crosses),  $t_2=t_1 = 0.3$  (lled triangles), and  $t_2=t_1 = 0.1$  (open squares). The band lling is (a) n = 0.475 and (b) n = 0.525.

The Tomonaga{Luttinger parameter K (V) changes most rapidly in the region  $2 < V=t_1 < 4$  where the quarter-lled system undergoes the charge-ordering transition. For  $V=t_1 > 4$ , we can interpret the system as a doped CDW insulator. In this region, we not that the dependence of K on the nearest-neighbor interaction  $V=t_1$  is much weaker. This can be understood from the Taylor expansion of K for a slightly doped CDW insulator. Above the transition point (V > V\_c) we generally expect<sup>19</sup> that for = 1=2 n 1 we have

$$K \quad (t_2; U; V; 1=2 ) = K^{C D W} \quad (t_2; V) + \frac{1}{h(t_2; U; V)} +$$
(26)

where  $t_1$  is used as energy unit. The prefactor h ( $t_2\,;U\,;V$ ) diverges exponentially at the critical interaction strength  $V_c$  but it rapidly tends to a constant for large V.

For in nitesim aldoping, the Tom onaga {Luttinger parameter of the CDW insulator K <sup>CDW</sup> ( $t_2=t_1;V=t_1$ ) also displays a smooth behavior as a function of V= $t_1$  and  $t_2=t_1$ . In Fig. 8 we show K <sup>CDW</sup> ( $t_2=t_1;V=t_1$ ) for U = 1 and various dimerizations. As for the case of a nite doping we see that the dimerization tends to reduce the Tom onaga {Luttinger parameter. In the CDW phase this tendency is somewhat compensated by the in uence of the nearest-neighbor C oulom b interaction which, for large interactions and for sm alldoping of the CDW state, delocalizes the holes over the system and therefore increases the charge uctuations which determ ine K via eq. (7).

;

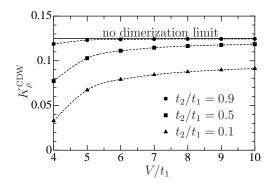


FIG. 8: Tom onaga{Luttinger parameter for the in nitesimally doped CDW insulator K<sup>CDW</sup> as a function of V=t<sub>1</sub> for t<sub>2</sub>=t<sub>1</sub> = 0:9, t<sub>2</sub>=t<sub>1</sub> = 0:5, and t<sub>2</sub>=t<sub>1</sub> = 0:1 at U=t<sub>1</sub> = 1. The solid line corresponds to K<sup>CDW</sup> = 1=8 when the dimerization is absent (t<sub>1</sub> = t<sub>2</sub>), and the dotted lines are guides for the eyes.

The most important observation is the magnitude of the Tom onaga{Luttinger parameter for the doped insulators. For in nitesimal doping we nd K = 1=8 in the absence of dimerization and even K < 1=8 in the presence of a dimerization. These small numbers persist for

nite doping, as seen in Fig. 7. Therefore, depending on the choice of the dimerization and the nearest-neighbor C oulomb interaction, one can easily nd parameter regions where 0.1 < K < 0.3 can be realized for slightly doped quarter-lled chains.

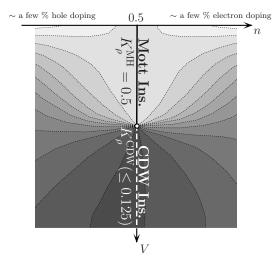


FIG. 9: Schematic phase diagram of the dimerized extended Hubbard model around quarter lling as a function of n and V. Variations of K are displayed by contour lines. Darker (brighter) color denotes smaller (larger) values of K.

Fig. 9 sum marizes our notings for the Tom onaga{ Luttingerparam eter in a schem atic phase diagram for the slightly doped quarter-lled dimerized extended H ubbard m odel. The M ott{Hubbard insulator (CDW insulator) can be characterized as  $2k_F$ -SDW ( $4k_F$ -CDW) states at quarter lling. Hence, the  $2k_F$ -SDW and  $4k_F$ -CDW cor-

relations are dom inant for slightly doped M ott{H ubbard and CDW insulators, respectively, and their correlation functions decay algebraically with the asymptotical behavior C<sup>2k<sub>F</sub>-SDW</sup> (r) r<sup>1 K</sup> for M ott{H ubbard insulators and C<sup>4k<sub>F</sub>-CDW</sup> (r) r<sup>4K</sup> for CDW insulators. Thus, the value K = 1=3 discrim inates the two types of (doped) insulators at nite doping. For an in nitesim ally doped insulator we correctly nd K (V = V<sub>dc</sub>) = 1=3 for V<sub>dc</sub> = V<sub>c</sub> but V<sub>dc</sub> becom es actually sm aller upon doping, as seen in Fig. 9.

#### C. Comparison with experiment

At last, we com pare our theoretical result with experiments on (TMTTF)<sub>2</sub>X. The electron transferm atrix elem ents<sup>37</sup> are estimated to be  $(t_1; t_2) = (137 \text{ m eV}; 93 \text{ m eV})$ for  $X = PF_6$ ,  $(t_1; t_2) = (140 \text{ m eV}; 100 \text{ m eV})$  for  $X = C D_4$ , and  $(t_1; t_2) = (133 \text{ m eV}; 119 \text{ m eV})$  for  $X = Br, ie_1, t_2 = t_1 =$ 0:68;0:71;0:89 for  $X = PF_6$ , C  $D_4$ , Br, respectively. From the comparison with the optical gap<sup>38,39</sup> the Coulomb param eters are estim ated to be  $U = t_1$ 7**:**0 and V*=*⊈ 2:8 for (TMTTF)<sub>2</sub>PF<sub>6</sub>. A comparison with Fig. 7 and 9 shows that this parameter set leads to K 0:25, in agreement with experimental estimates for the Tom onaga { Luttinger parameter from the tem perature dependence of the resistivity  $^{6,40}$ . In view of the CDW  $100 \,\mathrm{K}^{41,42,43}$ , the neareststate observed below T neighbor interaction could be even larger than  $V = t_1 = 2.8$ which would further reduce K  $\,$  .

Unfortunately, such values for the nearest-neighbor interaction  $V=t_1$  appear to contradict the results for the e ective exchange interaction as deduced from the high-tem perature data from the electron-spin-resonance (ESR) measurements<sup>44</sup>,  $J_{exp} = 420 \text{ K}$ ;430 K;500 K for the anions  $X = PF_6$ , C D 4, Br, respectively. In the presence of the dimerization and at quarter band-lling we can start from the e ective extended single-band Hubbard model (12) and the spin degrees of freedom can be described in terms of the e ective Heisenberg Ham iltonian (16). For  $U=t_1 = 7:0$ , the bare Hubbard model, V = 0 in (17), gives  $J_e$  (V = 0) = 499K; 564K; 841K. The good agreem ent of the experim ental and theoretical data for V = 0 implies that the nearest-neighbor interaction ought to be rather small. In particular, the a value V =  $2.8t_1$  for (TM TTF)<sub>2</sub>PF<sub>6</sub>, leads to J<sub>e</sub> (V =  $2:8t_1) = 222 \text{ K}$ , a factor of two sm aller than the experimental estimate. Additinally, with small V to adjust J<sub>exp</sub>, the resulting theoretical prediction for K 0:5 from Fig. 7 is not compatible with the experim ental estim ate, 0.2 < K < 0.3.

In order to reconcile this discrepancy we note that, in the ESR m easurem ents, the curves are tted to provide a good agreement with the Eggert{A eck{Takahashi m odel<sup>45</sup> for the spin susceptibility of the S = 1=2 antiferrom agnetic H eisenberg chain at elevated tem peratures. However, substantial deviations occur for sm all tem peratures, T < 100 K. They could be the result

of a dimensional crossover<sup>46</sup> and the transition to the CDW phase. We are tempted to attribute the deviations to an electrical larger nearest-neighbor interaction at low temperatures. Recall that our electronic model is purely one-dimensional, and neither covers the in unce of phonons<sup>47,48</sup> nor does it give an account on the screening of the electron-electron interaction which may change drastically in the vicinity of the transition to the CDW state. Therefore, temperature may have a quite substantial in unce on the value of the electric V-parameter in ourm odel so that eq. (17) cannot be applied with the values for V=t<sub>1</sub> at T = 0 to explain the susceptibility data for T > 100 K.

In fact, in the CDW phase, the e ective exchange interaction is given by  $J_e^{CDW} = t_1 \qquad 4\frac{4}{2} = (2UV^2)$  which results in  $J_e^{CDW} = 14K$  if we use the parameters for  $(TMTTF)_2PF_6$ . If the spin susceptibility could be measured in the (one-dimensional) CDW phase, the exchange interaction should be an order of magnitude sm aller than in the high-tem perature phase.

In  $(TM T SF)_2 PF_6$ , the hopping am plitudes are estimated as  $(t_1 = 252; m eV; t_2 = 209 m eV)$  and the elective C oulom b interactions are found to be weaker,  $U = t_1$ 5. Again, a weak nearest-neighbor C oulom b interaction,  $V_1 = 0.5t_1$ , would account for an exchange interaction  $J_e = 1.2$  1<sup>3</sup>CK which is compatible with the high-temperature experimental observation  $J_{exp} = 1.4$  1<sup>3</sup>CK.

#### IV. SUMMARY

U sing the DMRG method, we provided numerically exact results for the spin excitations, the CDW order parameter, and the Tom onaga {Luttinger parameter of the one-dimensional dimerized extended Hubbard model at and near commensurate llings.

In the presence of a dimerization we con m numerically that gap for the spin excitation is nite at half band-lling. However, the gap immediately disappears when the system is doped in nitesimally because there is no mechanism which con nest he holes to a single dimer. This result is qualitatively consistent with a rapid suppression of the spin gap with Zn doping in the spin-Peierls Heisenberg system CuGeO<sub>3</sub><sup>49</sup>, irrespective of the diculty in metalization this material<sup>50</sup>.

For the Tom onaga{Luttinger parameter the e ects of the dimerization are weak in the absence of the nearestneighbor Coulom b interaction V and away from quarter

lling. At and near quarter lling, the low er P eierls band is essentially half lled and the dim erized H ubbard m odel at lling n = 1=2 can be understood qualitatively and

even sem i-quantitatively in terms of an e ective singleband Hubbard model at electron density 2n. From the result of the corresponding Hubbard model at half band-

lling it immediately follows that K = 1=2 holds for the dimerized Hubbard model at in nitesimally doping away from quarter lling. Therefore, the Tomonaga { Luttinger parameter for the weakly doped quarter-lled system sensitively depends on the strength of the dimerization. In general, the dimerization tends to reduce K gradually because the elective scattering processes within the Peierls bands increase with the size of the Peierls gap.

In the presence of the nearest-neighbor C oulom b interaction, the case of quarter lling also deserves special attention because the M ott{H ubbard insulator goes over to a CDW insulator with a nite spin gap at a critical interaction strength V<sub>c</sub>. The dimerization opposes the form ation of the CDW phase, for example, the critical nearest-neighbor interaction shifts from V<sub>c</sub>=t<sub>1</sub> 2:65 in the absence of dimerization to V<sub>c</sub>=t<sub>1</sub> = 4 in the dimer limit.

The suppression of the charge order at quarter lling by the dimerization is rejected in a tendency to stabilize the metallic state by the dimerization away from quarter band-lling. However, the increase of the electronelectron scattering by the nearest-neighbor C oulomb interaction overcomes that tendency and results in a net reduction of K as a function of the dimerization and the nearest-neighbor interaction, see Fig. 7. As a consequence, fairly small values, K 0.25, can be obtained for a moderate ve-percent doping of the quarter-

lled dim erized extended Hubbard model at moderate Coulom b couplings,  $U = t_1 = 6$ ,  $V = t_1 = 3$ .

It is di cult to reconcile all experim ental data for the Bechgaard salts with our ndings for the dimerized extended Hubbard model in one dimension. In order to nd sm all values for the Tom onaga {Luttinger parameter, the Coulom b interactions must be large enough to reach the region of a (doped) CDW insulator which is not easily reconciled with the high-tem perature data for the exchange interaction. We suspect that the one-dimensional dimerized extended Hubbard model is still too sim plistic to describe the physics of the Bechgaard salts adequately.

#### A cknow ledgm ents

W e thank E.Jeckelm ann for useful discussions. S.E. is supported by the Honjo International Scholarship Foundation.

- <sup>1</sup> T. Ishiguro, K. Yam a ji, and G. Saito, Organic Superconductors (Springer, Berlin, 1998).
- tors, Vol. II, ed. by K. H. Bennem ann and J.B. Ketterson (Springer, Berlin, 2003), p. 453.
- <sup>2</sup> M. Lang and J. Muller, The Physics of Superconduc-
- $^3\,$  V . Vescoli, L . Degiorgi, W . Henderson, G . G runer, K P .

Starkey, and L.K. M ontgom ery, Science 281, 1181 (1998).

- <sup>4</sup> B. Dardel, D. Malterre, M. Grioni, P. Weibel, Y. Baer, J. Voit, and D. Jerome, Europhys. Lett. 24, 687 (1993).
- <sup>5</sup> F.Zwick, S.Brown, G.Margaritondo, C.Merlic, M.Onellion, J.Voit, and M.Grioni, Phys. Rev. Lett. 79, 3982 (1997).
- <sup>6</sup> J. Moser, M. Gabay, P. Auban-Senzier, D. Jerome, K. Bechgaard, and JM. Fabre, Eur. Phys. J. B 1, 39 (1998).
- <sup>7</sup> M. D ressel, A. Schwartz, G. G runer, and L. Degiorgi, Phys. Rev. Lett. 77, 398 (1996); A. Schwarz, M. D ressel, G. G runer, V. Vescoli, L. Degiorgi, and T. G iam archi, Phys. Rev. B 58, 1261 (1998).
- <sup>8</sup> G. M ihaly, I. Kezsmarki, F. Zamborszky, and L. Forro, Phys. Rev. Lett. 74, 2670 (2000).
- <sup>9</sup> J. Moser, J.R. Cooper, D. Jerome, B. Alavi, S.E. Brown, and K. Bechgaard, Phys. Rev. Lett. 84, 2674 (2000).
- <sup>10</sup> C.Bourbonnais, J.Phys. I (France) 3, 143 (1993).
- <sup>11</sup> P.W zietek, F.Creuzet, C.Bourbonnais, D.Jerome, K. Bechgaard, and P.Batail, J.Phys.I (France) 3, 171 (1993).
- <sup>12</sup> T.Lorenz, M.Hofmann, M.Gruninger, A.Freimuth, G.S. Uhrig, M.Dumm, and M.Dressel, Nature 418, 614 (2002).
- <sup>13</sup> S. Nishim oto, M. Takahashi, and Y. Ohta, J. Phys. Soc. Jpn. 69, 1594 (2000).
- <sup>14</sup> F.M ila and X.Zotos, Europhys. Lett. 24, 133 (1993).
- <sup>15</sup> K.Penc and F.M ila, Phys.Rev.B 50, 11429 (1994).
- <sup>16</sup> M. Hase, I. Terasaki, and K. Uchinokura, Phys. Rev. Lett. 70, 3651 (1993).
- <sup>17</sup> Density-M atrix Renorm alization, ed. by I. Peschel, X. W ang, M. Kaulke, and K. Hallberg (Springer, Berlin, 1999).
- <sup>18</sup> U.Schollwock, Rev.M od.Phys.77,259 (2005).
- <sup>19</sup> S. E jim a, F. Gebhard, and S. Nishimoto, Europhys. Lett. 70, 492 (2005).
- <sup>20</sup> H J.Schulz, Phys. Rev. Lett. 64, 2831 (1990).
- <sup>21</sup> H. Frahm and V.E. Korepin, Phys. Rev. B 42, 10553 (1990).
- <sup>22</sup> M.D zierzawa in The Hubbard M odel, ed.by D.Baeriswyl, DK.Campbell, JM P.Camelo, F.Guinea, and E.Louis, NATO ASI Ser. B, Vol. 343 (Plenum Press, New York 1995), p. 327.
- <sup>23</sup> R M . Noack, S. D aul, and S. K neer in Ref. [17], p. 197.
- <sup>24</sup> S.Dauland R M .Noack, Phys.Rev.B 58, 2635 (1998).
- <sup>25</sup> R.T.Clay, A.W. Sandvik, and D.K.Campbell, Phys.Rev. B 59, 4665 (1999).
- <sup>26</sup> J.Solyom, Adv.Phys. 28, 209 (1979).
- <sup>27</sup> T.Giam archi, Quantum Physics in One D in ension (Clarendon Press, Oxford, 2004).
- <sup>28</sup> S. Andergassen, T. Enss, V. Meden, W. Metzner, U. Schollwock, and K. Schonhammer, Phys. Rev. B 73, 045125 (2006).
- <sup>29</sup> T.Giam archi, Physica B 230-232, 975 (1997); T.Gia-

marchiand A.J.M illis, Phys.Rev.B 46, 9325 (1992).

- <sup>30</sup> JW .Bray, LV. Interrante, IS. Jacobs, and JC. Bonner, The spin-Peierls transition (Technical Information Series, New York, 1981).
- <sup>31</sup> S.N ishim oto and Y.O hta, Phys. Rev. B 59, 4738 (1999).
- <sup>32</sup> M.Tsuchiizu, H.Yoshioka, and Y.Suzum ura, J.Phys.Soc. Jpn. 70, 1460 (2001).
- <sup>33</sup> Y.Shibata, S.N ishim oto, and Y.O hta, Phys. Rev. B 64, 235107 (2001).
- <sup>34</sup> R.T.Clay, S.M azum dar, and D.K.Cam pbell, Phys.Rev. B 67, 115121 (2003).
- <sup>35</sup> K.Sano and Y.Ono, Phys. Rev. B 70, 155102 (2004).
- <sup>36</sup> H J. Schulz in Strongly Correlated Electronic M aterials, ed.by K S.Bedellet al. (A ddison-W esley, R eading, 1994), p.187.
- <sup>37</sup> L. Ducasse, M. Abderrabba, J. Hoarau, M. Pesquer, B. Gallois, and J. Gaultier, J. Phys. C 19, 3805 (1986); L. Ducasse, M. Abderrabba, B. Gallois, and D. Chasseau, Synth. M et. 19, 327 (1987).
- <sup>38</sup> F.M ila, Phys. Rev. B 52, 4788 (1995).
- <sup>39</sup> H.Benthien and E.Jeckelm ann, Eur.Phys.J.B 44, 287 (2005).
- <sup>40</sup> B.Korin-Ham zic, E.Tafra, M.Basletic, A.Ham zic, and M.Dressel, Phys. Rev. B 73, 115102 (2006).
- <sup>41</sup> F. Zam borszky, W. Yu, W. Raas, S.E. Brown, B. A lavi, C.A. Merlic, and A. Baur, Phys. Rev. B 66, 081103 (R) (2002).
- <sup>42</sup> F. Nad, P. Monceau, C. Carcel, and J.M. Fabre, Phys. Rev. B 62, 1753 (2000).
- <sup>43</sup> D S. Chow, F. Zam borszky, B. A lavi, D J. Tantillo, A. Baur, C A. M erlic, and S E. Brown, Phys. Rev. Lett. 89, 1698 (2000).
- <sup>44</sup> M. Dumm, A. Loidl, B.W. Fravel, K.P. Starkey, L.K. Montgomery, and M. Dressel, Phys. Rev. B 61, 511 (2000); M. Dumm, A. Loidl, B. A lavi, K.P. Starkey, L.K. Montgomery, and M. Dressel, Phys. Rev. B 62, 6512 (2000).
- <sup>45</sup> S. Eggert, I. A eck, and M. Takahashi, Phys. Rev. Lett. 73, 332 (1994).
- <sup>46</sup> M.D ressel, K.Petukhov, B.Salameh, P.Zomoza, and T. Giamarchi, Phys. Rev. B 71, 075104 (2005).
- <sup>47</sup> R.T.C lay and R.P.H ardikar, Phys. Rev. Lett. 95, 096401 (2005).
- <sup>48</sup> P. Maurel and M-B. Lepetit, Phys. Rev. B 62, 10744 (2000).
- <sup>49</sup> S.B. Osero, S-W. Cheong, B. Aktas, M.F. Hundley, Z. Fisk, and L.W. Rupp, Jr., Phys. Rev. Lett. 74, 1450 (1995).
- <sup>50</sup> I. Terasaki, R. Itti, N. Koshizuka, M. Hase, I. Tsukada, and K. Uchinokura, Phys. Rev. B 52, 295 (1995).